

PATENT ABSTRACTS OF JAPAN

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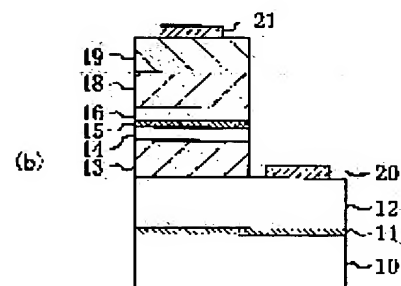
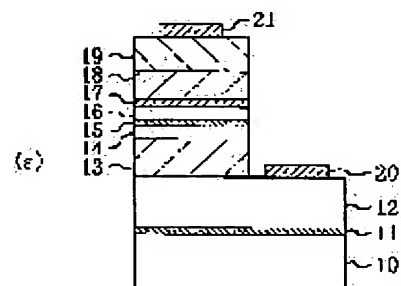
(21)Application number : 10-054634 (71)Applicant : MATSUSHITA ELECTRIC IND CO LTD
(22)Date of filing : 06.03.1998 (72)Inventor : HASEGAWA YOSHITERU
ISHIBASHI AKIHIKO
TSUJIMURA AYUMI
KIDOGUCHI ISAO
MIYANAGA RYOKO
KAMIYAMA SATOSHI
KUME MASAHIRO
BAN YUZABURO

(54) MANUFACTURE OF SEMICONDUCTOR AND SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To form a p-n junction having a steep dopant profile in a gallium nitride semiconductor.

SOLUTION: On a sapphire substrate 10, an n-type GaN contact layer 12, an n-type Al_{0.1}Ga_{0.9}N clad layer 13, a first GaN light guide layer 14, an In_{0.20}Ga_{0.80}N quantum well active layer 15, and a second GaN light guide layer 16 are successively formed. On the upper surface of the second light guide layer 16, an Al_{0.1}Ga_{0.9}N diffusion suppressing layer 17 having a film thickness of 20 nm and doped with Mg as a p-type dopant and Si as an n-type dopant is formed and, on the upper surface of the layer 17, a p-type Al_{0.1}Ga_{0.9}N clad layer 18 is formed.



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